

Silicon NPN Power Transistors

2N6077 2N6078 2N6079

DESCRIPTION

- With TO-66 package
- Low collector-emitter saturation voltage
- High breakdown voltage

APPLICATIONS

- For horizontal deflection output stages of TV's and CRT's

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

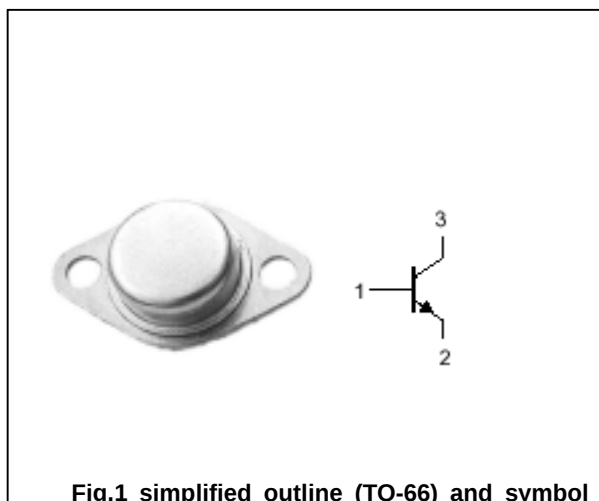


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6077	Open emitter	275	V
		2N6078		250	
		2N6079		350	
V_{CEO}	Collector-emitter voltage	2N6077	Open base	300	V
		2N6078		275	
		2N6079		375	
V_{EBO}	Emitter-base voltage		Open collector	6	V
I_C	Collector current			7	A
P_D	Total Power Dissipation		$T_C = 25$	45	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	4.28	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sus)}	Collector-emitter sustaining voltage	2N6077	I _C =0.1A ; I _B =0	275			V
		2N6078		250			
		2N6079		350			
V _{CEsat}	Collector-emitter saturation voltage		I _C =5A; I _B =0.5A			1.0	V
V _{BEsat}	Collector-emitter saturation voltage		I _C =5A; I _B =0.5A			1.2	V
I _{CEO}	Collector cut-off current		V _{CE} = Rated V _{CEO} ; I _B =0			2.0	mA
I _{CEX}	Collector cut-off current		V _{CE} =Rated V _{CEO} ; V _{BE(off)} =1.5V T _C =125			0.1 1.0	mA
I _{CBO}	Collector cut-off current		V _{CB} =Rated V _{CBO} ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current		V _{EB} =6V; I _C =0			1.0	mA
h _{FE}	DC current gain		I _C =1.2A ; V _{CE} =1V	12		70	
f _T	Transition frequency		I _C =0.5A; V _{CE} =10V; f=1MHz		7		MHz

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PACKAGE OUTLINE

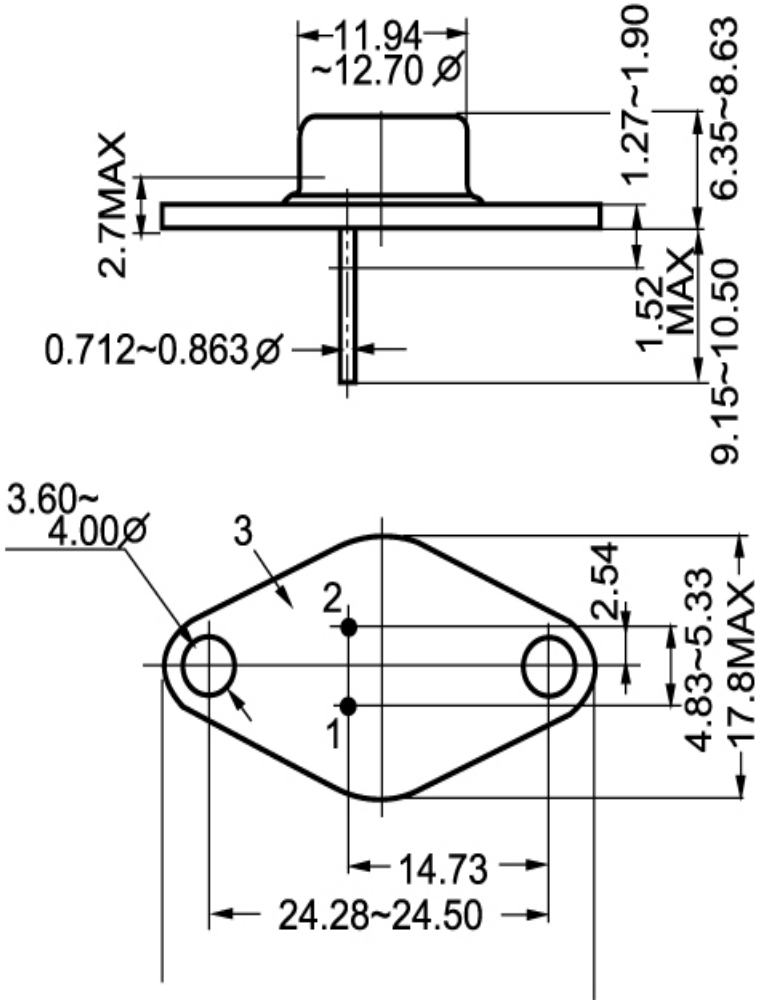


Fig.2 outline dimensions